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Retraction: Integrating Epitaxial-Like Pb(Zr,Ti)O₃ Thin-Film into Silicon for Next-Generation Ferroelectric Field-Effect Transistor

Jae Hyo Park, Hyung Yoon Kim, Gil Su Jang, Ki Hwan Seok, Hee Jae Chae, Sol Kyu Lee, Zohreh Kiaee & Seung Ki Joo

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This Article has been retracted by the authors. The data presented in Figures 1e, 1g, 1h, 2b-d, 4a-b, 4d-e, 6a-b and 7a-b were manipulated and are duplicated in other papers¹⁻⁵.

All authors acknowledge these issues and agree to the retraction of the Article.

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